



SI7898DP-T1-GE3 Information



For Reference Only

Part Number SI7898DP-T1-GE3 Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 150V 3A PPAK SO-8

Package PowerPAK? SO-8

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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SI7898DP-T1-GE3 Specifications

Manufacturer Part Number SI7898DP-T1-GE3 Manufacturer Vishay Siliconix Category Discrete Semiconductor Products		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package PowerPAK? SO-8 Series TrenchFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 150V Current - Continuous Drain (Id) @ 25°C 3A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 1nput Capacitance (Ciss) (Max) @ Vds - Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs Rds On (Max) @ Id, Vgs Smohm @ 3.5A, 10V Operating Temperature Jupiler Device Package PowerPAK? SO-8 PowerPAK? SO-8 PowerPAK? SO-8	Manufacturer Part Number	SI7898DP-T1-GE3
Package PowerPAK? SO-8 Series TrenchFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 150V Current - Continuous Drain (Id) @ 25°C 3A (Ta) Drive Voltage (Max Rds On, Min Rds On) 6V, 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 21nC @ 10V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.9W (Ta) Rds On (Max) @ Id, Vgs 85 mOhm @ 3.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 Package / Case PowerPAK? SO-8	Manufacturer	Vishay Siliconix
PackagePowerPAK? SO-8SeriesTrenchFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)150VCurrent - Continuous Drain (Id) @ 25°C3A (Ta)Drive Voltage (Max Rds On, Min Rds On)6V, 10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs2lnC @ 10VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±20VFET Feature-Power Dissipation (Max)1.9W (Ta)Rds On (Max) @ Id, Vgs85 mOhm @ 3.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePowerPAK? SO-8Package / CasePowerPAK? SO-8	Category	Discrete Semiconductor Products
Series TrenchFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 3A (Ta) Drive Voltage (Max Rds On, Min Rds On) 6V, 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 21nC @ 10V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.9W (Ta) Rds On (Max) @ Id, Vgs 85 mOhm @ 3.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 Package / Case		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)150VCurrent - Continuous Drain (Id) @ 25°C3A (Ta)Drive Voltage (Max Rds On, Min Rds On)6V, 10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs21nC @ 10VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±20VFET Feature-Power Dissipation (Max)1.9W (Ta)Rds On (Max) @ Id, Vgs85 mOhm @ 3.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePowerPAK? SO-8Package / CasePowerPAK? SO-8	Package	PowerPAK? SO-8
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)150VCurrent - Continuous Drain (Id) @ 25°C3A (Ta)Drive Voltage (Max Rds On, Min Rds On)6V, 10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs21nC @ 10VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±20VFET Feature-Power Dissipation (Max)1.9W (Ta)Rds On (Max) @ Id, Vgs85 mOhm @ 3.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePowerPAK? SO-8Package / CasePowerPAK? SO-8	Series	TrenchFET?
Drain to Source Voltage (Vdss)150VCurrent - Continuous Drain (Id) @ 25°C3A (Ta)Drive Voltage (Max Rds On, Min Rds On)6V, 10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs21nC @ 10VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±20VFET Feature-Power Dissipation (Max)1.9W (Ta)Rds On (Max) @ Id, Vgs85 mOhm @ 3.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePowerPAK? SO-8Package / CasePowerPAK? SO-8	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 6V, 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 21nC @ 10V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) #20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 85 mOhm @ 3.5A, 10V Operating Temperature Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 Package / Case	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)6V, 10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs21nC @ 10VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±20VFET Feature-Power Dissipation (Max)1.9W (Ta)Rds On (Max) @ Id, Vgs85 mOhm @ 3.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePowerPAK? SO-8Package / CasePowerPAK? SO-8	Drain to Source Voltage (Vdss)	150V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 PowerPAK? SO-8	Current - Continuous Drain (Id) @ 25°C	3A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case PowerPAK? SO-8	Drive Voltage (Max Rds On, Min Rds On)	6V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.9W (Ta) Rds On (Max) @ Id, Vgs 85 mOhm @ 3.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 Package / Case PowerPAK? SO-8	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)1.9W (Ta)Rds On (Max) @ Id, Vgs85 mOhm @ 3.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePowerPAK? SO-8Package / CasePowerPAK? SO-8	Gate Charge (Qg) (Max) @ Vgs	21nC @ 10V
FET Feature - Power Dissipation (Max) 1.9W (Ta) Rds On (Max) @ Id, Vgs 85 mOhm @ 3.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 Package / Case PowerPAK? SO-8	Input Capacitance (Ciss) (Max) @ Vds	-
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 85 mOhm @ 3.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 Package / Case PowerPAK? SO-8	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs 85 mOhm @ 3.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 Package / Case PowerPAK? SO-8	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 Package / Case PowerPAK? SO-8	Power Dissipation (Max)	1.9W (Ta)
Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 Package / Case PowerPAK? SO-8	Rds On (Max) @ Id, Vgs	85 mOhm @ 3.5A, 10V
Supplier Device Package PowerPAK? SO-8 Package / Case PowerPAK? SO-8	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case PowerPAK? SO-8	Mounting Type	Surface Mount
•	Supplier Device Package	PowerPAK? SO-8
Report errors?	Package / Case	PowerPAK? SO-8
		Report errors?

SI7898DP-T1-GE3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SI7898DP-T1-GE3 Payment Methods



















SI7898DP-T1-GE3 Shipping Methods













If you have any question about SI7898DP-T1-GE3, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com